

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	197	((thin adj film adj transistor) tft) same (cmos complementary) same (channel with ("p-type" "p-doped" type dop\$4))) same ((impurit\$4 dop\$4 boron "p-type" "p type") near4 concentration)	US-PGPUB; USPAT	OR	ON	2004/11/27 14:43
L2	0	"6632711".URPN.	USPAT	OR	OFF	2004/11/27 14:34
L3	4	"6635521".URPN.	USPAT	OR	OFF	2004/11/27 15:06
L4	142	((thin adj film adj transistor) tft) and (cmos complementary) and (channel with ("p-type" "p-doped" type dop\$4))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/27 15:10
L5	112	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls. 345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and ((thin adj film adj transistor) tft) and ((cmos complementary) same (channel near4 ("p-type" "p-doped" dop\$4)))	US-PGPUB; USPAT	OR	ON	2004/11/27 15:16
L6	1039	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls. 345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and (channel with (impurit\$4 dop\$4) with ("p-type" "p type" "p-doped" "p doped" boron))	US-PGPUB; USPAT	OR	ON	2004/11/27 15:54
L7	190	((thin adj film adj transistor) tft) same (cmos complementary) same (channel with (impurit\$4 dop\$4) with ("p-type" "p type" "p-doped" "p doped" boron))	US-PGPUB; USPAT	OR	ON	2004/11/27 15:24
L8	24	((channel with (impurit\$4 dop\$4) with ("p-type" "p type" "p-doped" "p doped" boron))) and ((thin adj film adj transistor) tft) and (cmos complementary)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/27 15:40
L9	123	((channel near4 (impurit\$4 dop\$4) with ("p-type" "p type" "p-doped" "p doped" boron))) same ((thin adj film adj transistor) tft cmos complementary)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/27 15:44
L10	87	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls. 345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and ((thin adj film adj transistor) tft) and ((cmos complementary) same (channel with (impurit\$4 dop\$4) with ("p-type" "p type" "p-doped" "p doped" boron)))	US-PGPUB; USPAT	OR	ON	2004/11/27 15:48